L Number	Hits	Search Text	DB	Time stamp
1	102	((438/3,253,254,238,239,396).CCLS.) and buried near3 contact and ferroelectric and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:26
2	5586	ferroelectric adj memory	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:26
3	41	(((438/3,253,254,238,239,396).CCLS.) and buried near3 contact and ferroelectric and contact adj hole) and (ferroelectric adj memory)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:27
4	1	((257/295,298,310,532).CCLS.) and (insulat$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:51
5	78	((((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric) and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:53
6	273	buried near3 contact and ferroelectric and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:54
7	15	buried near3 (contact near3 structure) and ferroelectric and contact adj hole	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:54
8	46	insulat$3 and substrate and contact adj hole and (burry or burried)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:58
9	0	(ferroelectric adj memory) and (insulat$3 and substrate and contact adj hole and (burry or burried))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 10:58
10	3088	(((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:03
11	46	(((silicon adj oxynitride) "SiON") or ((silicon adj nitride) "SiN")) and (((257/295,298,310,532).CCLS.) and buried near3 contact) and ferroelectric and plug with (tungsten 'W')	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:01
12	750	((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:02

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13	49	(ferroelectric adj memory) and (((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) (aluminum adj oxide) "SiOn" "SiN" "AlO"))) and dram)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:02
14	53	(ferroelectric adj memory) and ((((blocking adj layer) (etch adj stop)) near9 ((silicon adj nitride) (silicon adj oxinitride) "SiOn" SiN)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/07/22 11:03